

N-channel MOS-FET

250V 0,12Ω 30A 150W

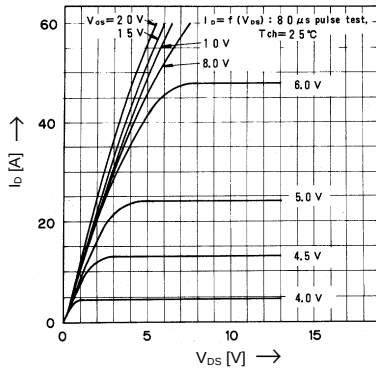
2SK1277

F-V Series

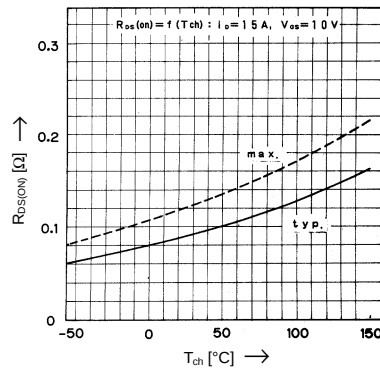
FUJI
ELECTRIC

> Characteristics

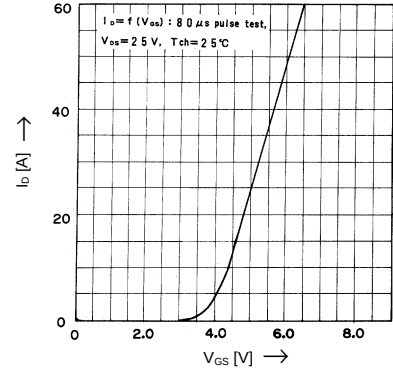
Typical Output Characteristics



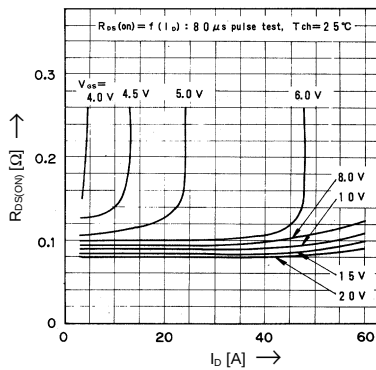
Drain-Source-On-State Resistance vs. T_{ch}



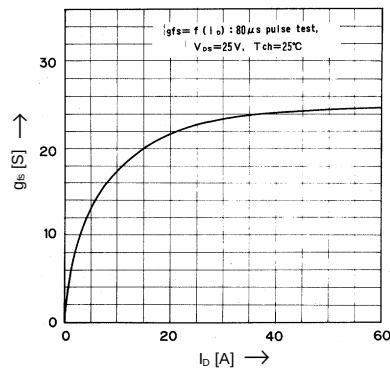
Typical Transfer Characteristics



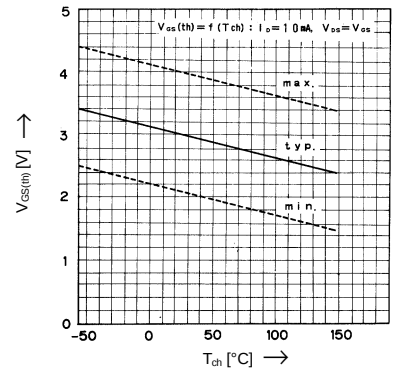
Typical Drain-Source-On-State-Resistance vs. I_D



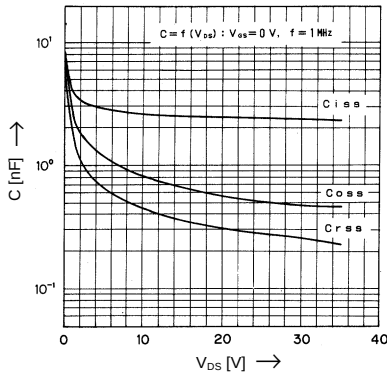
Typical Forward Transconductance vs. I_D



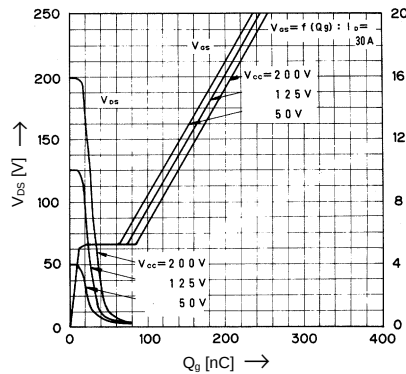
Gate Threshold Voltage vs. T_{ch}



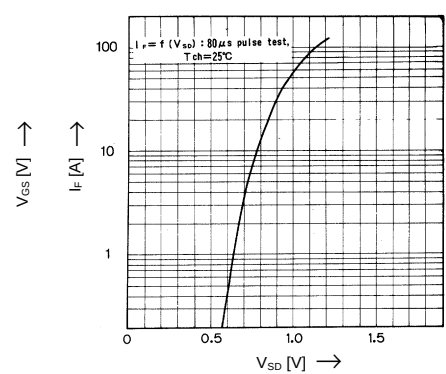
Typical Capacitance vs. V_{DS}



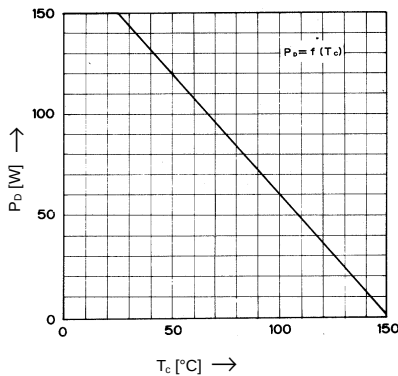
Typical Input Charge



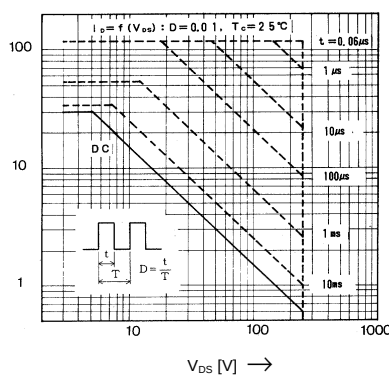
Forward Characteristics of Reverse Diode



Allowable Power Dissipation vs. T_c



Safe operation area



Transient Thermal impedance

